

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

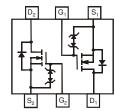
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)





SOT26

Top View



Top View Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2004DMK-7	SOT26	3,000/Tape & Reel

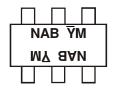
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Alalogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} \mathsf{NAB} = \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \overline{\mathsf{Y}} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{T} = 2006) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$

Date Code Key

Notes:

Year	2006	~	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	Т	~	D	E	F	G	Н	_	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Symbol	Value	Units		
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	ID	540 390	mA
Pulsed Drain Current (Note 6)			I _{DM}	1.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	225	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	556	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						·
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	—	±1	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
		_	0.4 0.5	0.55 0.70	Ω	V _{GS} = 4.5V, I _D = 540mA
Static Drain-Source On-Resistance	R _{DS(ON)}					$V_{GS} = 2.5V, I_D = 500mA$
			0.7	0.9		V _{GS} = 1.8V, I _D = 350mA
Forward Transfer Admittance	Y _{FS}	200	_		ms	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage (Note 7)	V _{SD}	0.5		1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						·
Input Capacitance	CISS		_	150	pF	
Output Capacitance	C _{OSS}			25	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}			20	pF	

Notes:

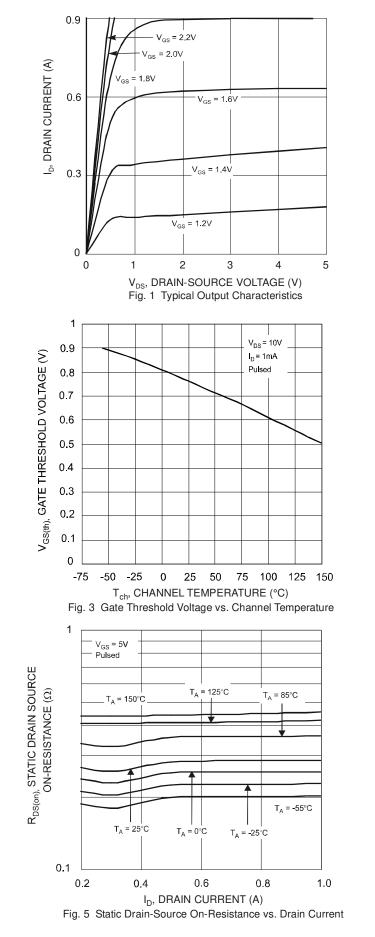
5.

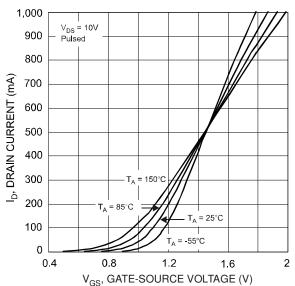
6.

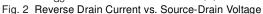
Device mounted on FR-4 PCB. Pulse width $\leq 10\mu$ S, Duty Cycle $\leq 1\%$. Short duration pulse test used to minimize self-heating effect.

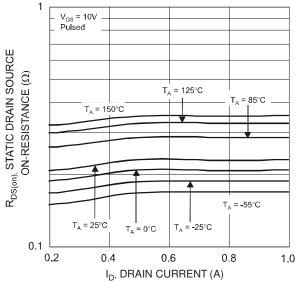
7. 8. Guaranteed by design. Not subject to product testing.



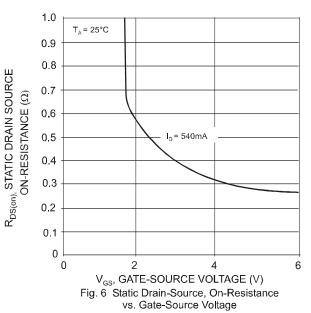






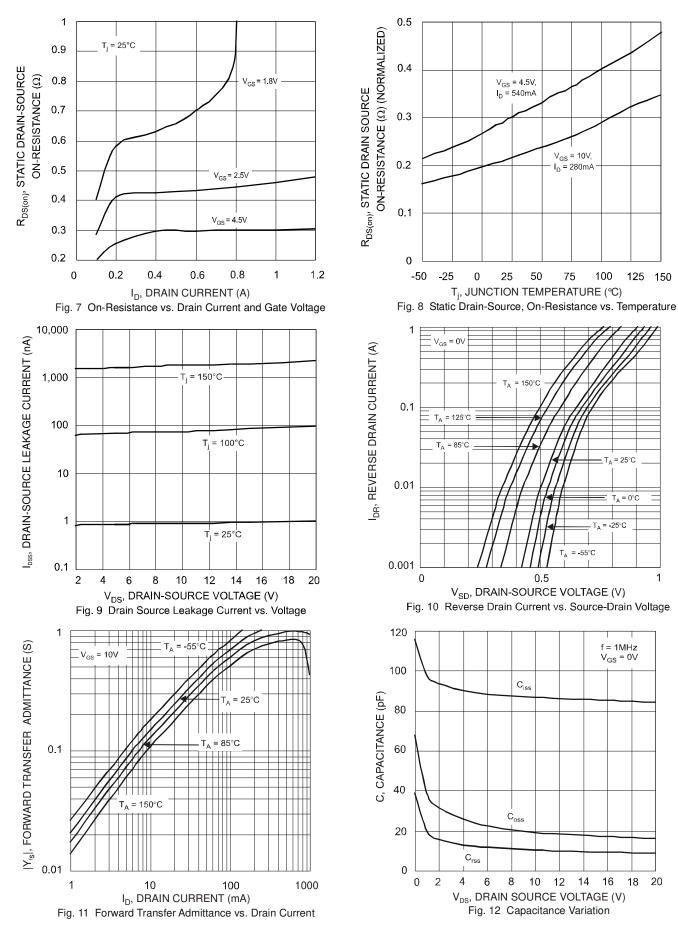








DMN2004DMK

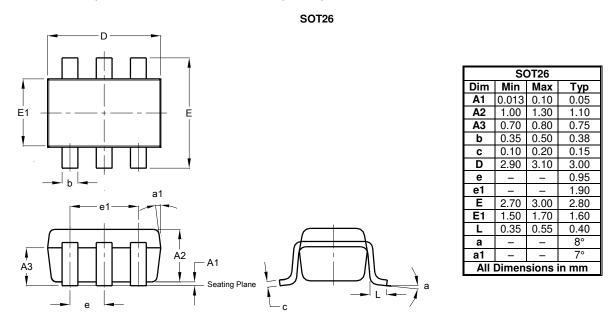


DMN2004DMK Document number: DS30937 Rev. 5 - 2



Package Outline Dimensions

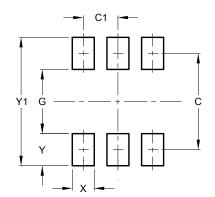
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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